

2SD2213

Silicon NPN Epitaxial, Darlington

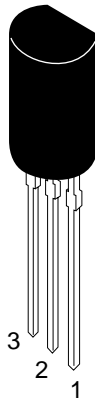
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Application

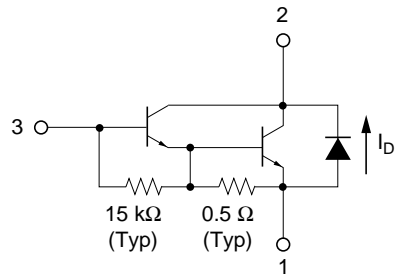
Low frequency power amplifier

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base



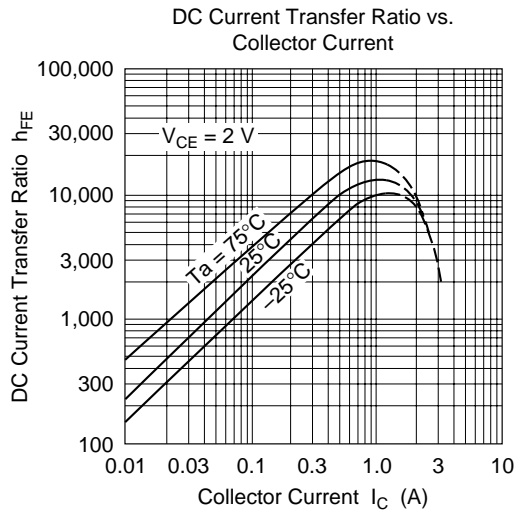
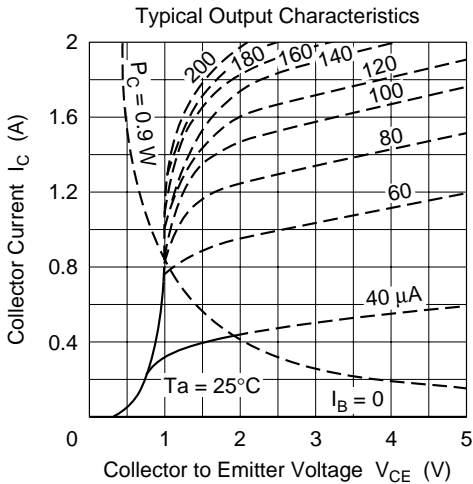
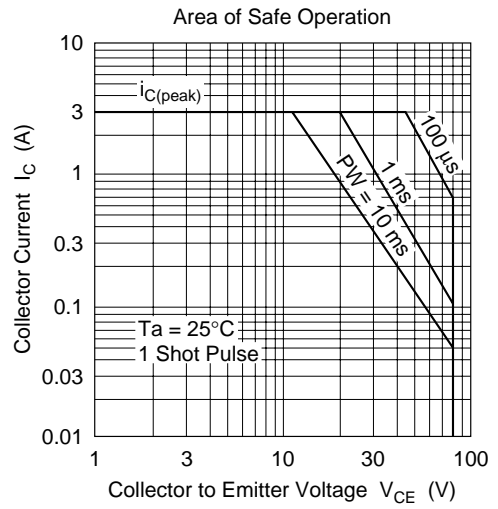
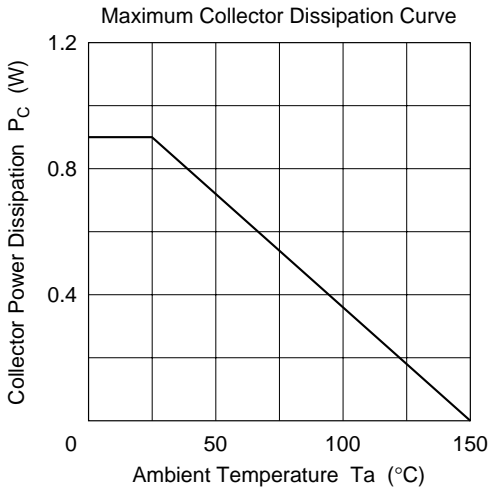
Absolute Maximum Ratings (Ta = 25°C)

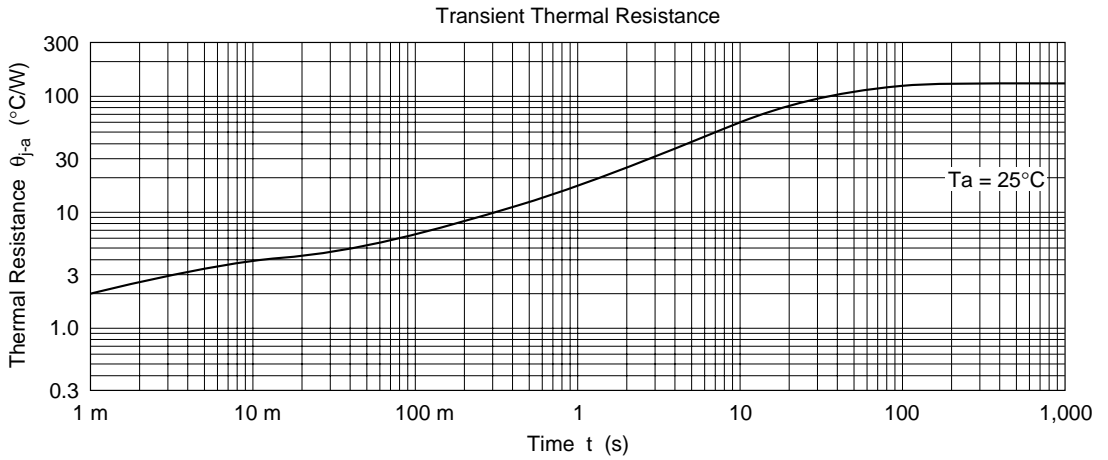
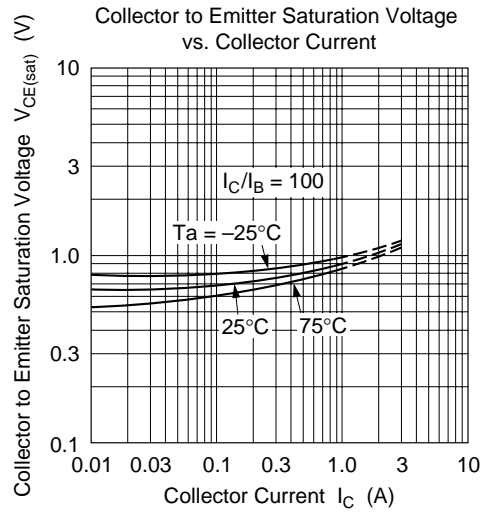
| Item | Symbol | Rated | Unit |
|------------------------------|----------------------|-------------|------|
| Collector to base voltage | V_{CBO} | 150 | V |
| Collector to emitter voltage | V_{CEO} | 80 | V |
| Emitter to base voltage | V_{EBO} | 8 | V |
| Collector current | I_C | 1.5 | A |
| Collector peak current | $i_{C(\text{peak})}$ | 3 | A |
| Collector power dissipation | P_C | 0.9 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |
| E to C diode forward current | I_D | 1.5 | A |

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|-----------------------------------------|----------------------|------|-----|-------|---------------|---------------------------------------------------|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 150 | — | — | V | $I_C = 1 \text{ mA}, I_E = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 80 | — | — | V | $I_C = 10 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 8 | — | — | V | $I_E = 50 \text{ mA}, I_C = 0$ |
| Collector cutoff current | I_{CBO} | — | — | 5.0 | μA | $V_{CB} = 120 \text{ V}, I_E = 0$ |
| | I_{CEO} | — | — | 5.0 | μA | $V_{CE} = 65 \text{ V}, I_E = \infty$ |
| DC current transfer ratio | h_{FE} | 2000 | — | — | | $V_{CE} = 2 \text{ V}, I_C = 0.15 \text{ A}^{*1}$ |
| | h_{FE} | 5000 | — | 30000 | | $V_{CE} = 2 \text{ V}, I_C = 1 \text{ A}^{*1}$ |
| | h_{FE} | 1000 | — | — | | $V_{CE} = 2 \text{ V}, I_C = 1.5 \text{ A}^{*1}$ |
| Collector to emitter saturation voltage | $V_{CE(\text{sat})}$ | — | — | 1.5 | V | $I_C = 1 \text{ A}^{*1}, I_B = 1 \text{ mA}$ |
| Base to emitter saturation voltage | $V_{BE(\text{sat})}$ | — | — | 2.0 | V | $I_C = 1 \text{ A}^{*1}, I_B = 1 \text{ mA}$ |
| E to C diode forward voltage | V_D | — | — | 3.0 | V | $I_D = 1.5 \text{ A}^{*1}$ |

Note: 1. Pulse test







| | |
|--------------------------|-----------|
| Hitachi Code | TO-92 Mod |
| JEDEC | — |
| EIAJ | Conforms |
| Weight (reference value) | 0.35 g |

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